- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- ***DOC*™ (Dynamic Output Control) Circuit Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation**
- **Dynamic Drive Capability Is Equivalent to Standard Outputs With I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}**
- **Overvoltage-Tolerant Inputs/Outputs Allow Mixed-Voltage-Mode Data Communications**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Package Options Include Plastic Thin Shrink Small-Outline (DGG) and Thin Very Small-Outline (DGV) Packages**

description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V_{OL} vs I_{OL} and V_{OH} vs I_{OH} curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number SCEA006, and *Dynamic Output Control (DOC™) Circuitry Technology and Applications*, literature number SCEA009.

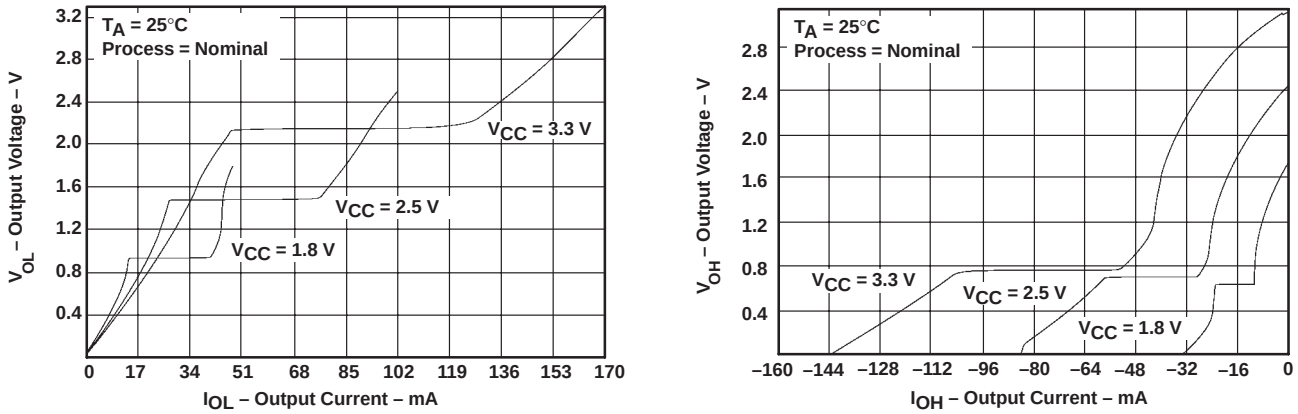

Figure 1. Output Voltage vs Output Current

This 18-bit universal bus transceiver is operational at 1.2-V to 3.6-V V_{CC}, but is designed specifically for 1.65-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B, but uses $\overline{\text{OEBA}}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{\text{OEBA}}$ is active low).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

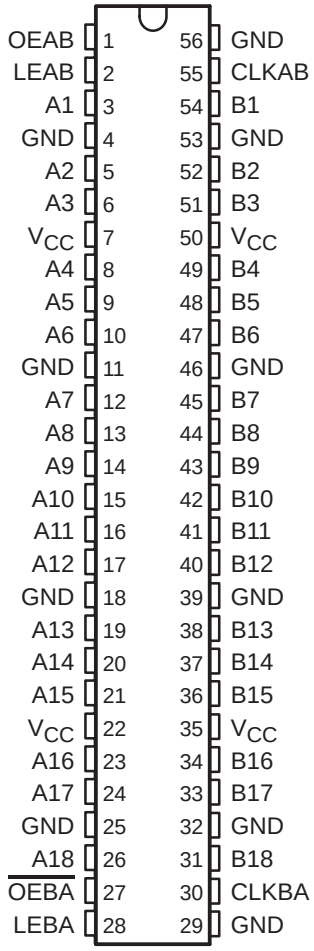
To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74AVC16501 is characterized for operation from –40°C to 85°C.

terminal assignments

DGG OR DGV PACKAGE
(TOP VIEW)

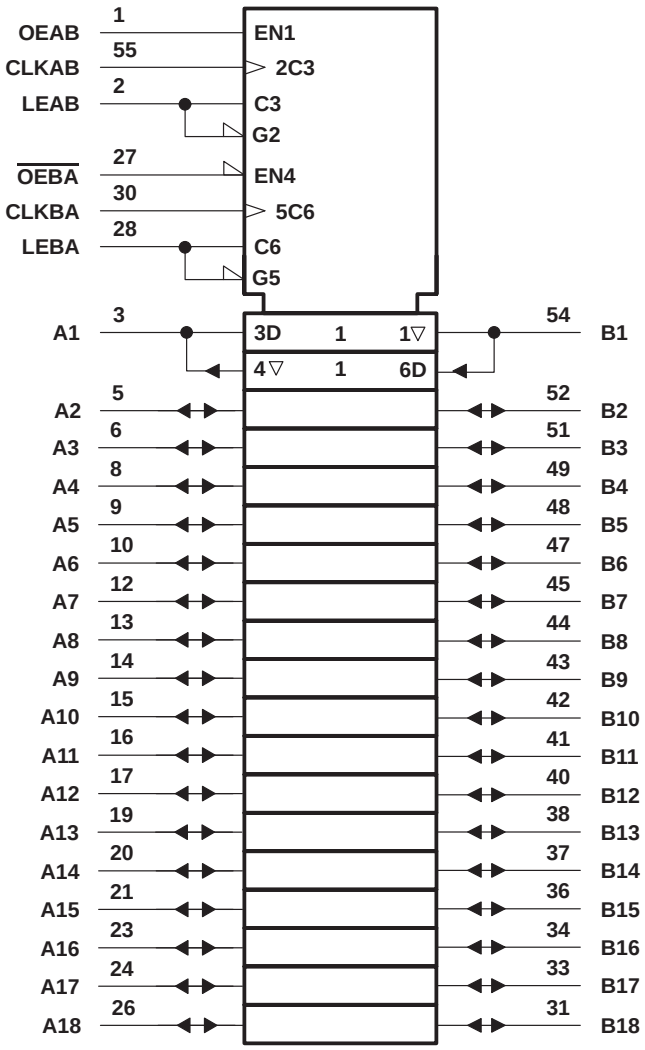


FUNCTION TABLE†
(each universal bus transceiver)

INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	L or H	X	B_0‡

† A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB is high before LEAB goes low

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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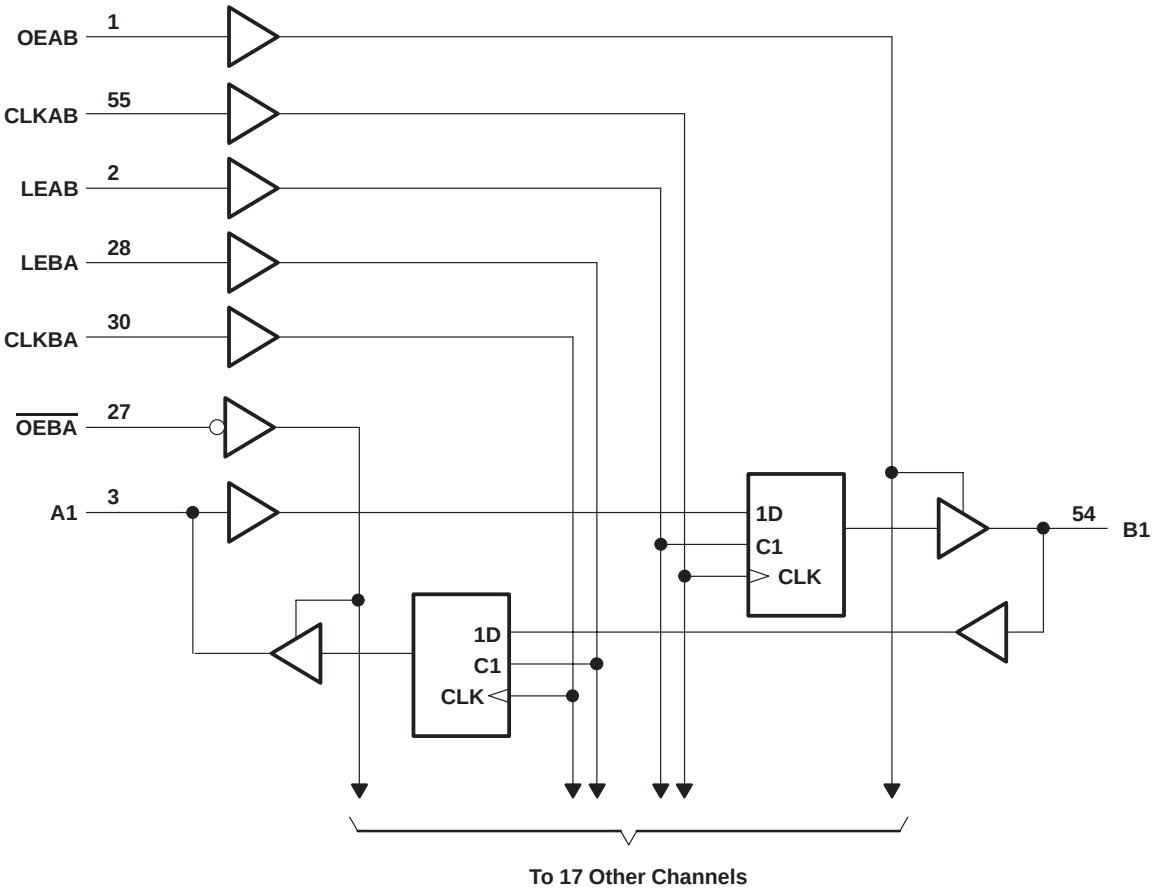
logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Voltage range applied to any input/output when the output is in the high-impedance or power-off state, V_O (see Note 1) . . . . . –0.5 V to 4.6 V
Voltage range applied to any input/output when the output is in the high or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 64°C/W
DGV package . . . . . 48°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.4	3.6	V
		Data retention only	1.2		
V_{IH}	High-level input voltage	V_{CC} = 1.2 V	V_{CC}		V
		V_{CC} = 1.4 V to 1.6 V	$0.65 \times V_{CC}$		
		V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$		
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 1.2 V		GND	V
		V_{CC} = 1.4 V to 1.6 V		$0.35 \times V_{CC}$	
		V_{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
V_I	Input voltage		0	3.6	V
V_O	Output voltage	Active state	0	V_{CC}	V
		3-state	0	3.6	
I_{OHS}	Static high-level output current†	V_{CC} = 1.4 V to 1.6 V		–2	mA
		V_{CC} = 1.65 V to 1.95 V		–4	
		V_{CC} = 2.3 V to 2.7 V		–8	
		V_{CC} = 3 V to 3.6 V		–12	
I_{OLS}	Static low-level output current†	V_{CC} = 1.4 V to 1.6 V		2	mA
		V_{CC} = 1.65 V to 1.95 V		4	
		V_{CC} = 2.3 V to 2.7 V		8	
		V_{CC} = 3 V to 3.6 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 1.4 V to 3.6 V		5	ns/V
T_A	Operating free-air temperature		–40	85	°C

† Dynamic drive capability is equivalent to standard outputs with I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}. See Figure 1 for V_{OL} vs I_{OL} and V_{OH} vs I_{OH} characteristics. Refer to the TI application reports, ***AVC Logic Family Technology and Applications***, literature number **SCEA006**, and ***Dynamic Output Control (DOC™) Circuitry Technology and Applications***, literature number **SCEA009**.

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OHS} = –100 µA		1.4 V to 3.6 V	V_{CC}–0.2			V
		I_{OHS} = –2 mA,	V_{IH} = 0.91 V	1.4 V	1.05			
		I_{OHS} = –4 mA,	V_{IH} = 1.07 V	1.65 V	1.2			
		I_{OHS} = –8 mA,	V_{IH} = 1.7 V	2.3 V	1.75			
		I_{OHS} = –12 mA,	V_{IH} = 2 V	3 V	2.3			
V_{OL}		I_{OLS} = 100 µA		1.4 V to 3.6 V			0.2	V
		I_{OLS} = 2 mA,	V_{IL} = 0.49 V	1.4 V			0.4	
		I_{OLS} = 4 mA,	V_{IL} = 0.57 V	1.65 V			0.45	
		I_{OLS} = 8 mA,	V_{IL} = 0.7 V	2.3 V			0.55	
		I_{OLS} = 12 mA,	V_{IL} = 0.8 V	3 V			0.7	
I_I	Control inputs	$V_I = V_{CC}$ or GND		3.6 V			±2.5	µA
I_{off}		V_I or V_O = 3.6 V		0			±10	µA
I_{OZ}‡		$V_O = V_{CC}$ or GND		3.6 V			±12.5	µA
I_{CC}		$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			40	µA
C_i	Control inputs	$V_I = V_{CC}$ or GND		2.5 V				pF
				3.3 V				
C_{io}	A or B ports	$V_O = V_{CC}$ or GND		2.5 V				pF
				3.3 V				

† Typical values are measured at V_{CC} = 2.5 V and 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

				V_{CC} = 1.2 V		V_{CC} = 1.5 V ± 0.1 V		V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency													MHz
t_w	Pulse duration	LE high												ns
		CLK high or low												
t_{su}	Setup time	Data before CLK↑												ns
		Data before LE↓	CLK high											
			CLK low											
t_h	Hold time	Data after CLK↑												ns
		Data after LE↓	CLK high or low											

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.2 V	V_{CC} = 1.5 V ± 0.1 V		V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}												MHz
t_{pd}	A or B	B or A										ns
	LE	A or B										
	CLK											
t_{en}	OEAB	B										ns
t_{dis}	OEAB	B										ns
t_{en}	$\overline{OEBA}$	A										ns
t_{dis}	$\overline{OEBA}$	A										ns

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	UNIT
				TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz				pF
		Outputs disabled					

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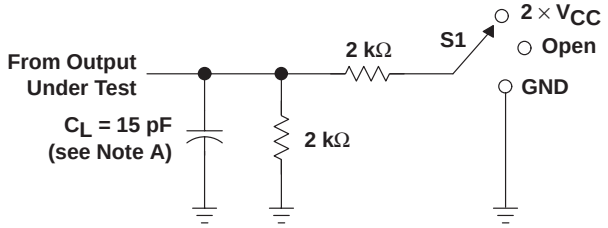
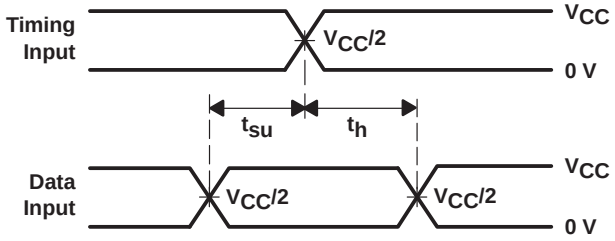
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.2 V AND 1.5 V ± 0.1 V

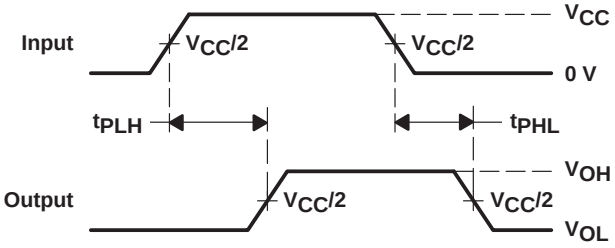


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

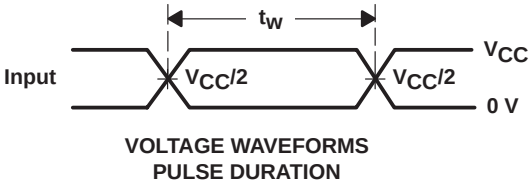
LOAD CIRCUIT



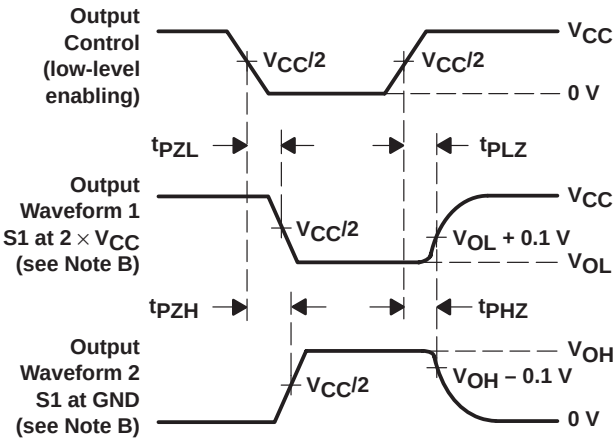
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

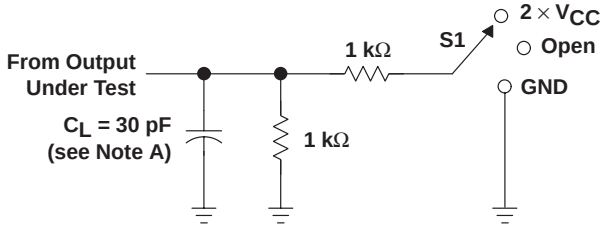


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

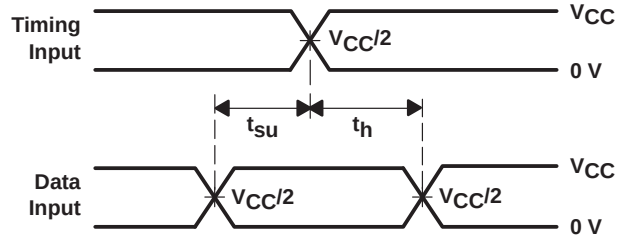
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V ± 0.15 V

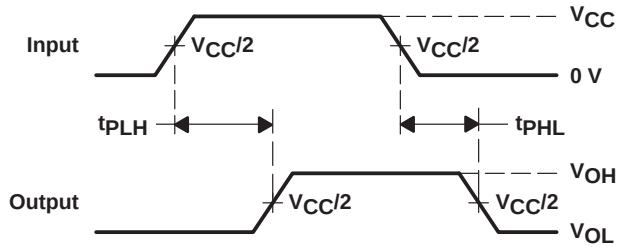


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

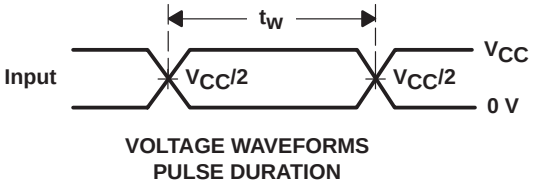
LOAD CIRCUIT



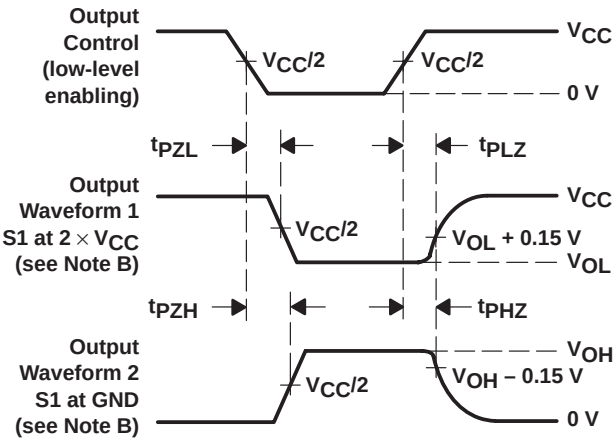
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

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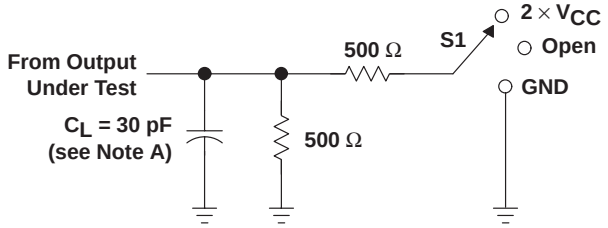
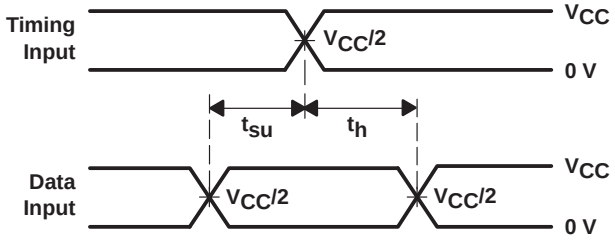
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

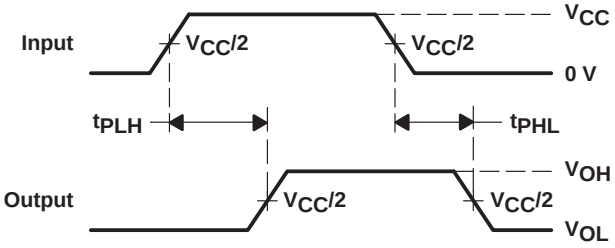


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

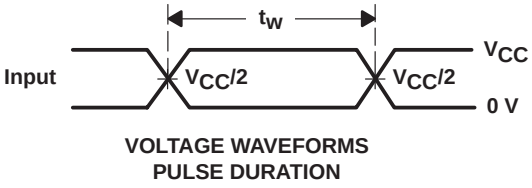
LOAD CIRCUIT



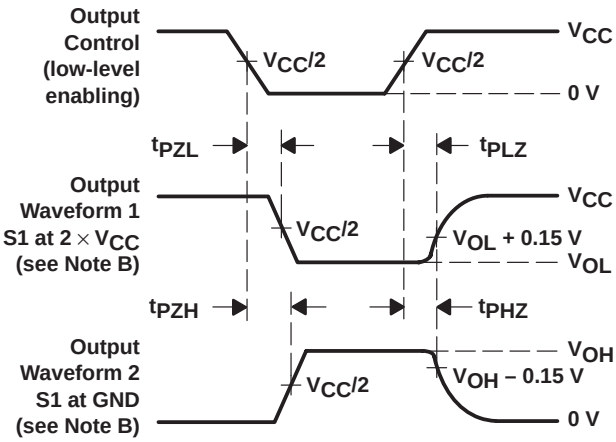
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

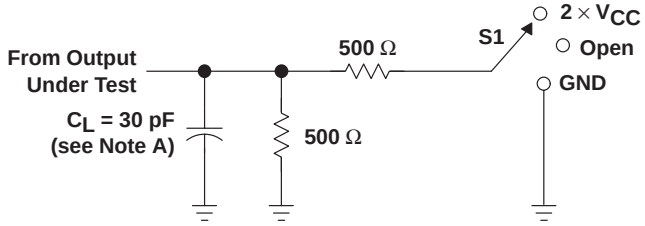


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

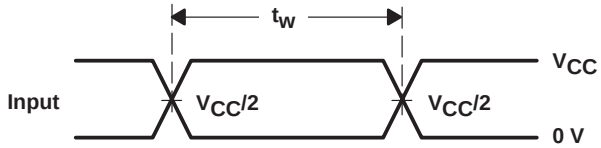
Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

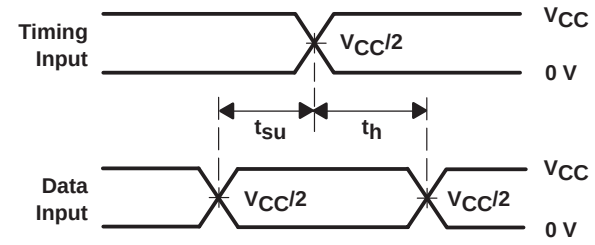


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

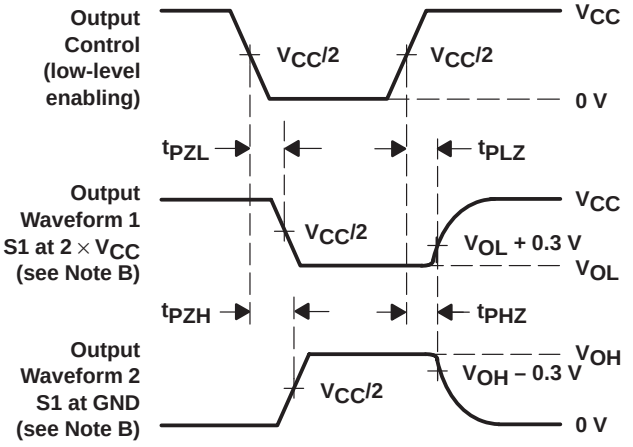
LOAD CIRCUIT



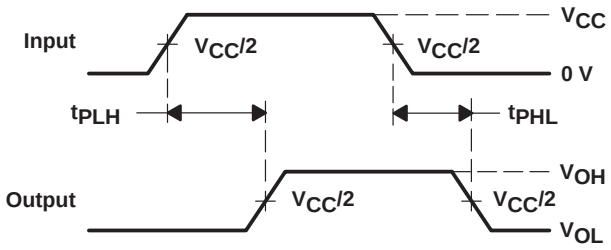
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 5. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

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